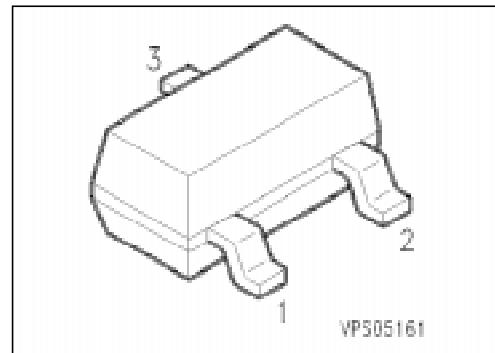


PNP Silicon Switching Transistors

**SMBT 2907
SMBT 2907 A**

- High DC current gain: 0.1 mA to 500 mA
- Low collector-emitter saturation voltage
- Complementary types: SMBT 2222,
SMBT 2222 A (NPN)



Type	Marking	Ordering Code (tape and reel)	Pin Configuration			Package ¹⁾
			1	2	3	
SMBT 2907	s2B	Q68000-A6501	B	E	C	SOT-23
SMBT 2907 A	s2F	Q68000-A6474				

Maximum Ratings

Parameter	Symbol	Values		Unit
		SMBT 2907	SMBT 2907 A	
Collector-emitter voltage	V_{CE0}	40	60	V
Collector-base voltage	V_{CB0}		60	
Emitter-base voltage	V_{EB0}		5	
Collector current	I_C		600	mA
Total power dissipation, $T_S = 77^\circ\text{C}$	P_{tot}		330	mW
Junction temperature	T_j		150	$^\circ\text{C}$
Storage temperature range	T_{stg}		– 65 ... + 150	

Thermal Resistance

Junction - ambient ²⁾	$R_{th JA}$	≤ 290	K/W
Junction - soldering point	$R_{th JS}$	≤ 220	

¹⁾ For detailed information see chapter Package Outlines.

²⁾ Package mounted on epoxy pcb 40 mm × 40 mm × 1.5 mm/6 cm² Cu.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC characteristics

Collector-emitter breakdown voltage $I_C = 10 \text{ mA}$	$V_{(\text{BR})\text{CE}0}$	40 60	— —	— —	V
Collector-base breakdown voltage $I_C = 10 \mu\text{A}$	$V_{(\text{BR})\text{CB}0}$	60 60	— —	— —	
Emitter-base breakdown voltage $I_E = 10 \mu\text{A}$	$V_{(\text{BR})\text{EB}0}$	5	—	—	
Collector cutoff current $V_{CB} = 50 \text{ V}$	I_{CB0}	—	—	20	nA
$V_{CB} = 50 \text{ V}$		—	—	10	nA
$V_{CB} = 50 \text{ V}, T_A = 150^\circ\text{C}$	SMBT 2907	—	—	20	μA
$V_{CB} = 50 \text{ V}, T_A = 150^\circ\text{C}$	SMBT 2907 A	—	—	10	μA
Emitter cutoff current $V_{EB} = 3 \text{ V}$	I_{EB0}	—	—	10	nA
DC current gain ¹⁾ $I_C = 100 \mu\text{A}, V_{CE} = 10 \text{ V}$	h_{FE}	35 75	— —	— —	—
$I_C = 1 \text{ mA}, V_{CE} = 10 \text{ V}$	SMBT 2907 SMBT 2907 A	50 100	— —	— —	
$I_C = 10 \text{ mA}, V_{CE} = 10 \text{ V}^1)$	SMBT 2907 SMBT 2907 A	75 100	— —	— —	
$I_C = 150 \text{ mA}, V_{CE} = 10 \text{ V}^1)$	SMBT 2907 SMBT 2907 A	100 100	— —	300 300	
$I_C = 500 \text{ mA}, V_{CE} = 10 \text{ V}^1)$	SMBT 2907 SMBT 2907 A	30 50	— —	— —	
Collector-emitter saturation voltage ¹⁾ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	$V_{CE\text{sat}}$	—	—	0.4	V
$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		—	—	1.6	
Base-emitter saturation voltage ¹⁾ $I_C = 150 \text{ mA}, I_B = 15 \text{ mA}$	$V_{BE\text{sat}}$	—	—	1.3	
$I_C = 500 \text{ mA}, I_B = 50 \text{ mA}$		—	—	2.6	

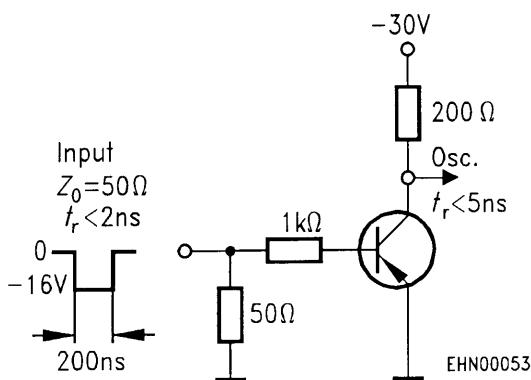
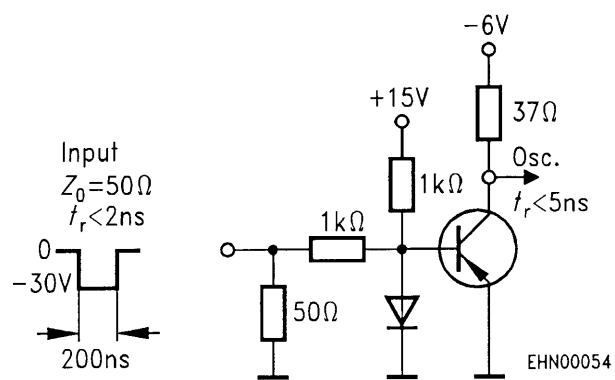
¹⁾ Pulse test conditions: $t \leq 300 \mu\text{s}$, $D = 2\%$.

Electrical Characteristicsat $T_A = 25^\circ\text{C}$, unless otherwise specified.

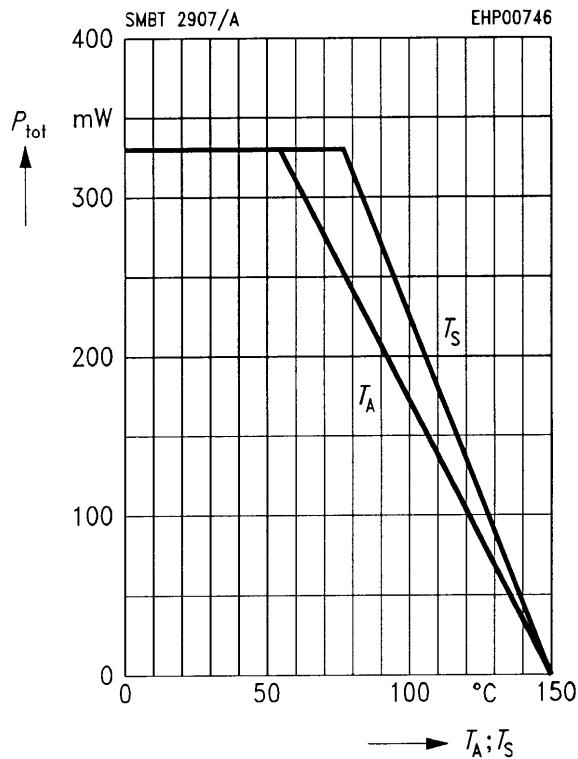
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

AC characteristics

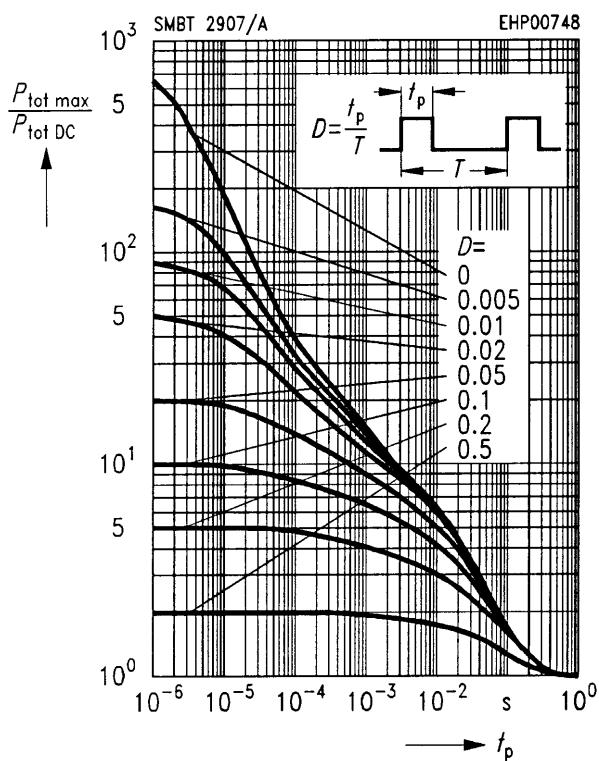
Transition frequency $I_C = 20 \text{ mA}, V_{CE} = 20 \text{ V}, f = 100 \text{ MHz}$	f_T	200	—	—	MHz
Output capacitance $V_{CB} = 10 \text{ V}, f = 1 \text{ MHz}$	C_{obo}	—	—	8	pF
Input capacitance $V_{EB} = 0.5 \text{ V}, f = 1 \text{ MHz}$	C_{ibo}	—	—	30	
$V_{CC} = 30 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = 15 \text{ mA}$					
Delay time	t_d	—	—	10	ns
Rise time	t_r	—	—	40	ns
$V_{CC} = 6 \text{ V}, I_C = 150 \text{ mA}, I_{B1} = I_{B2} = 15 \text{ mA}$					
Storage time	t_{stg}	—	—	80	ns
Fall time	t_f	—	—	30	ns

Test circuits**Delay and rise time****Storage and fall time**

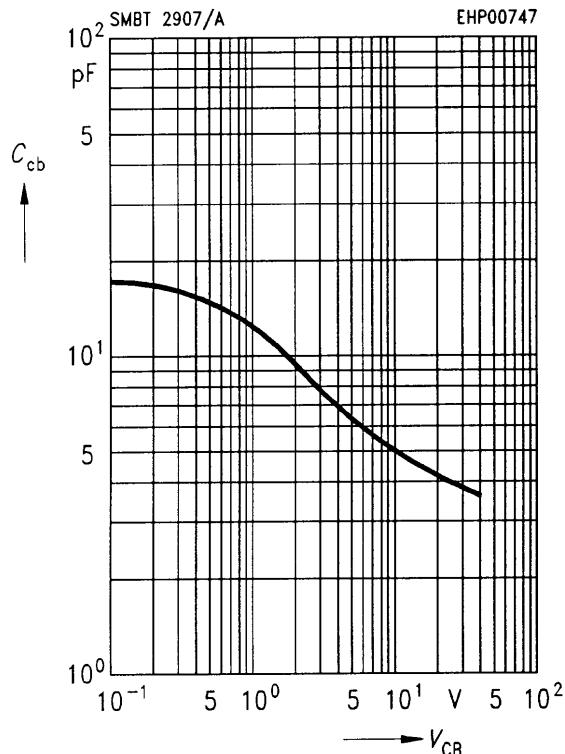
Total power dissipation $P_{\text{tot}} = f(T_A^*; T_S)$
 * Package mounted on epoxy



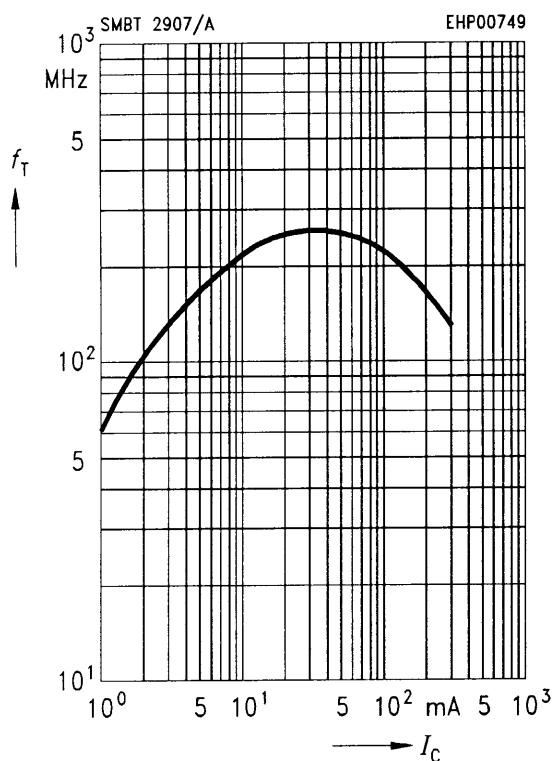
Permissible pulse load $P_{\text{tot max}}/P_{\text{tot DC}} = f(t_p)$



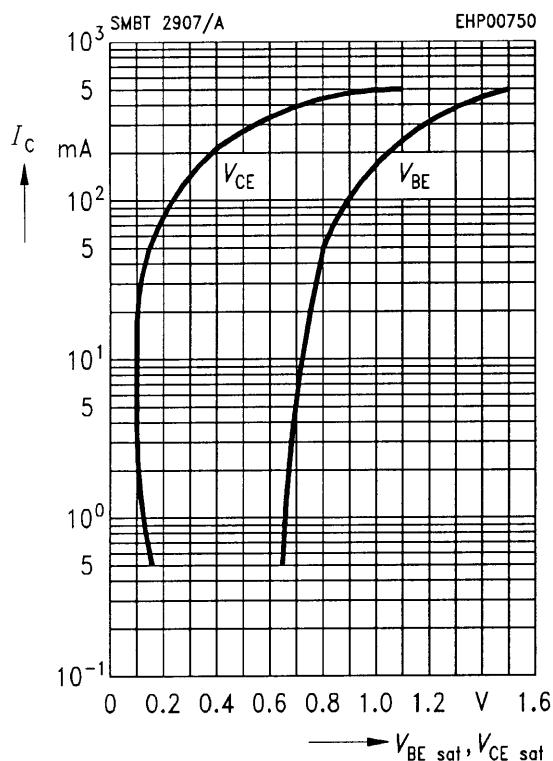
Collector-base capacitance $C_{\text{cb}} = f(V_{\text{CB}})$
 $f = 1 \text{ MHz}$



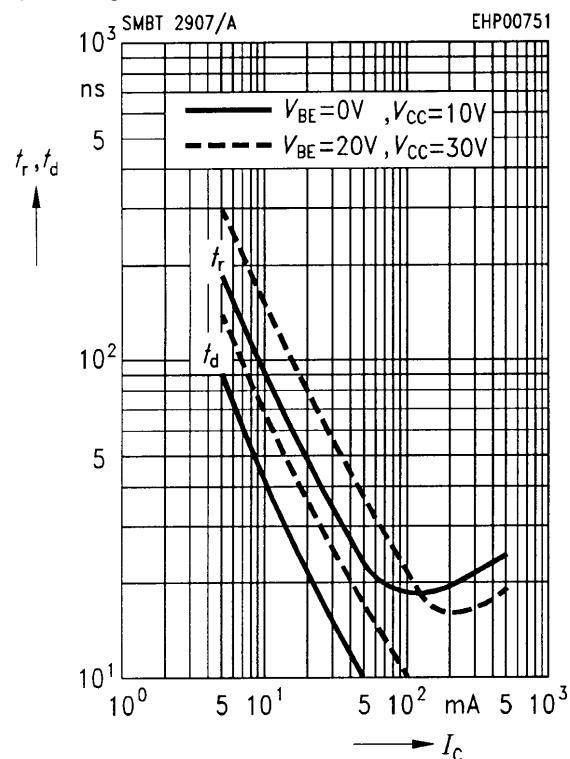
Transition frequency $f_T = f(I_C)$
 $V_{\text{CE}} = 20 \text{ V}$



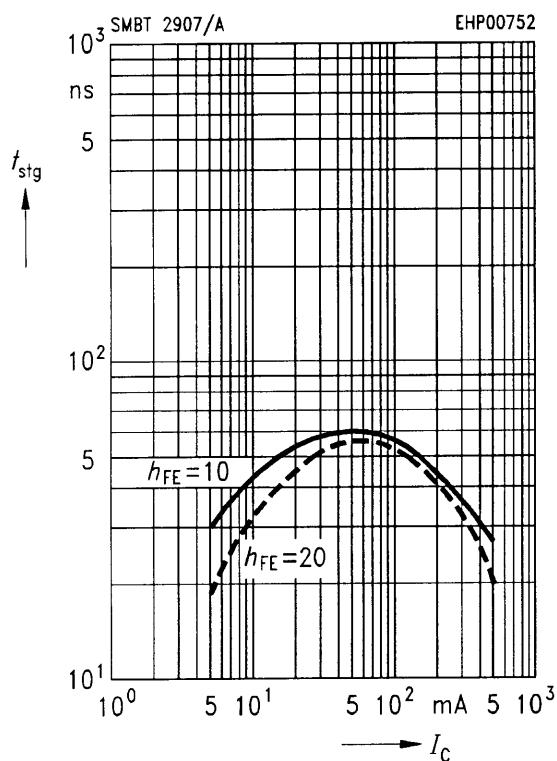
Saturation voltage $I_C = f(V_{BEsat}, V_{CEsat})$
 $h_{FE} = 10$



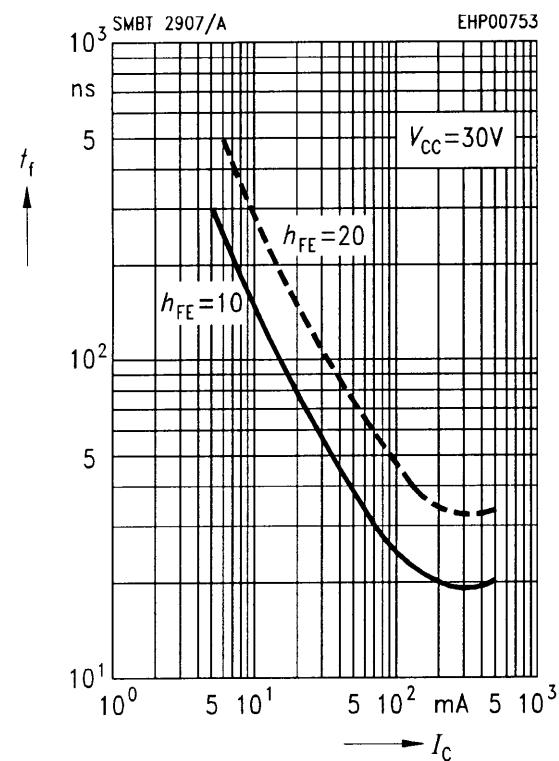
Delay time $t_d = f(I_C)$
Rise time $t_r = f(I_C)$
 $h_{FE} = 10$



Storage time $t_{stg} = f(I_C)$



Fall time $t_f = f(I_C)$



DC current gain $h_{FE} = f(I_C)$

